

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address COMMISSIONER FOR PATENTS
FO. Box 1/409 (1993)
All Patents (1994)
All Patents (

CONFIRMATION NO. 2769

1 SECTION FOR METERS AND TOTAL TO THE HOUSE AND THE SECTION IN

SERIAL NUMBER 10/526,059 **POPELICANTS** Alexandre Ellison, Linkoping, SWEDEN; Bjorn Magnusson, Linkoping, SWEDEN; Asko Vehanen, Esbo, FINLAND; Dietrich Stephani, Bubenreuth, GERMANY; Heinz Milehner, Ulterreuth, GERMANY; Peter Friedrichs, Numberg, GERMANY; Peter Friedrichs, Numberg, GERMANY; Peter Friedrichs, Numberg, GERMANY; Process of the second	ib Data Sheet									
APPLICANTS Alexandre Ellison, Linkoping, SWEDEN; Bjorn Magnusson, Linkoping, SWEDEN; Asko Vehanen, Esbo, FINLAND; Dietrich Stephani, Bubenreuth, GERMANY; Heinz Mitlehner, Utterreuth, GERMANY; Peter Friedrichs, Numberg, GERMANY; *** CONTINUING DATA**** This application is a 371 of PCT/SE03/01309 08/22/2003 *** FOREIGN APPLICATIONS*** SWEDEN 0202585-6 08/30/2003 Foreign Priority dailmed	. NUMBER 526,059	R DATE CLASS GRO						ATTORNEY DOCKET NO. 35947-213490		
Alexandre Ellison, Linkoping, SWEDEN; Bjorn Magnusson, Linkoping, SWEDEN; Asko Vehanen, Esbo, FINLAND; Dietrich Stephani, Bubenreuth, GERMANY; Heinz Mitlehner, Utterreuth, GERMANY; Peter Friedrichs, Nurnberg, GERMANY; ****CONTINUING DATA*** This application is a 371 of PCT/SE03/01309 08/22/2003 ****FOREIGN APPLICATIONS*** SWEDEN 0202585-6 08/30/2003 ***Foreign Priority daimed	1	RULE								
STATE OR COUNTRY SWEDEN State of Country Sweden or Country Sweden	Alexandre Ellison, Linkoping, SWEDEN; Bjorn Magnusson, Linkoping, SWEDEN; Asko Vehanen, Esbo, FINLAND; Dietrich Stephani, Bubenreuth, GERMANY; Heinz Mitlehner, Utterreuth, GERMANY; Peter Friedrichs, Nurnberg, GERMANY; ** CONTINUING DATA This application is a 371 of PCT/SE03/01309 08/22/2003									
26694 TITLE Lightly doped silicon carbide wafer and use thereof in high power devices	35 USC 119 (a-d) conditions					WING CL		AIMS	INDEPENDE CLAIMS 2	
Lightly doped silicon carbide wafer and use thereof in high power dones.				igh nower d	tevices		_			
	doped silicon ca	bide wafer and use	thereof in r	iigii powei c	evices			_		
☐ 1.16 Fees		EES: Authority has been given in Paper				All Fees 1.16 Fees (Filling)				
	NG FEE FEES					1.17 Fees (Processing Ext. of time)				
RECEIVED No to charge destribed solutions 1.18 Fees (Issue)		o to charge/credit DEFOSTI AGG for following:			,,,,,					
Other Credit		r					Other			